

[illegible]

17 near 6 ft

June 2005

	U	Inventor	Document	Issued	P	Title	Current	Current K	Retire	S	C	P	S	P	Image	Doc	P
1		Hsieh, Chia	US 6441429	2002	19	Spiral-gate flash memory device having	257/31	257/314		P	P	P	P	P		US 6441429	
2		Yang, Yu-Hsi	US 6153904	2000	10	Fabrication method for increasing the	257/31	257/E21.4		P	P	P	P	P		US 6153904	
3		Fukatsu, Sh	US 598680	1999	14	Semiconductor memory device	257/31	257/316		P	P	P	P	P		US 598680	
4		Takada, Kaz	US 664496	2003	2	Semiconductor device and method of	257/31	257/315		P	P	P	P	P		US 664496	
5		Chan, Lep e	US 6501122	2002	10	Flash device having a large planar area	257/31	257/314		P	P	P	P	P		US 6501122	
6		Choi, Jong	US 623990	2001	2	Flash memory device and method for	438/59	257/E21.4		P	P	P	P	P		US 623990	
7		Kim, Ki-Chu	US 200501	2005	12	Methods of erasing a non-volatile mem	365/18			P	P	P	P	P		US 200501	
8		Chu, Wen-Ti	US 200501	2005	11	METHOD TO FORM FLASH MEMORY WITH V	438/29	438/424		P	P	P	P	P		US 200501	
9		Eitan, Boaz	US 200501	2005	3	Two bit non-volatile electrically erasab	365/19	365/183.1		P	P	P	P	P		US 200501	
10		Yu, Suk-Wo	US 200501	2005	5	Semiconductor devices having at least	438/25			P	P	P	P	P		US 200501	